

#### **General description** 1.

The 74AUP1G34 provides a low-power, low-voltage single buffer.

Schmitt trigger action at all inputs makes the circuit tolerant to slower input rise and fall times across the entire  $V_{CC}$  range from 0.8 V to 3.6 V.

This device ensures a very low static and dynamic power consumption across the entire  $V_{CC}$  range from 0.8 V to 3.6 V.

This device is fully specified for partial power-down applications using I<sub>OFF</sub>. The I<sub>OFF</sub> circuitry disables the output, preventing the damaging backflow current through the device when it is powered down.

#### 2. **Features and benefits**

- Wide supply voltage range from 0.8 V to 3.6 V
- High noise immunity
- Complies with JEDEC standards:
  - JESD8-12 (0.8 V to 1.3 V)
  - JESD8-11 (0.9 V to 1.65 V)
  - JESD8-7 (1.2 V to 1.95 V)
  - JESD8-5 (1.8 V to 2.7 V)
  - JESD8-B (2.7 V to 3.6 V)
- ESD protection:
  - HBM JESD22-A114F Class 3A exceeds 5000 V
  - MM JESD22-A115-A exceeds 200 V
  - CDM JESD22-C101E exceeds 1000 V
- Low static power consumption;  $I_{CC} = 0.9 \mu A$  (maximum)
- Latch-up performance exceeds 100 mA per JESD 78 Class II
- Inputs accept voltages up to 3.6 V
- Low noise overshoot and undershoot < 10 % of V<sub>CC</sub>
- I<sub>OFF</sub> circuitry provides partial power-down mode operation
- Multiple package options
- Specified from –40 °C to +85 °C and –40 °C to +125 °C





### 3. Ordering information

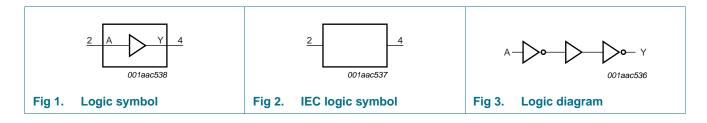
Type number	Type number Package										
	Temperature range	Name	Description	Version							
74AUP1G34GW	–40 °C to +125 °C	TSSOP5	plastic thin shrink small outline package; 5 leads; body width 1.25 mm	SOT353-1							
74AUP1G34GM	–40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 $\times$ 1.45 $\times$ 0.5 mm	SOT886							
74AUP1G34GF	–40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 $\times$ 1 $\times$ 0.5 mm	SOT891							
74AUP1G34GN	–40 °C to +125 °C	XSON6	extremely thin small outline package; no leads; 6 terminals; body $0.9 \times 1.0 \times 0.35$ mm	SOT1115							
74AUP1G34GS	–40 °C to +125 °C	XSON6	extremely thin small outline package; no leads; 6 terminals; body $1.0 \times 1.0 \times 0.35$ mm	SOT1202							

### 4. Marking

Table 2. Marking	
Type number	Marking code <sup>[1]</sup>
74AUP1G34GW	aN
74AUP1G34GM	aN
74AUP1G34GF	aN
74AUP1G34GN	aN
74AUP1G34GS	aN

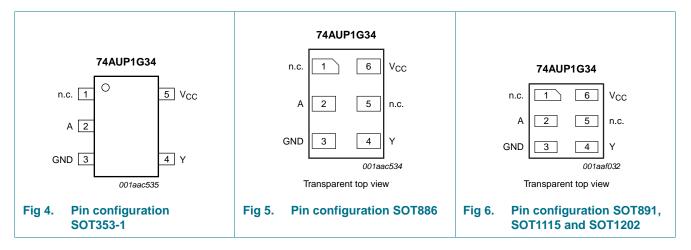
[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

### 5. Functional diagram



### 6. Pinning information

### 6.1 Pinning



### 6.2 Pin description

Table 3.     Pin description										
Symbol	Pin		Description							
	TSSOP5	XSON6								
n.c.	1	1	not connected							
А	2	2	data input A							
GND	3	3	ground (0 V)							
Y	4	4	data output Y							
n.c.	-	5	not connected							
V <sub>CC</sub>	5	6	supply voltage							

## 7. Functional description

#### Table 4. Function table<sup>[1]</sup>

Input	Output
A	Y
L	L
Н	Н

[1] H = HIGH voltage level;

L = LOW voltage level.

### 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>CC</sub>	supply voltage		-0.5	+4.6	V
I <sub>IK</sub>	input clamping current	V <sub>I</sub> < 0 V	-50	-	mA
VI	input voltage		<u>[1]</u> –0.5	+4.6	V
I <sub>OK</sub>	output clamping current	V <sub>O</sub> < 0 V	-50	-	mA
Vo	output voltage	Active mode and Power-down mode	<u>[1]</u> –0.5	+4.6	V
lo	output current	$V_{O} = 0 V$ to $V_{CC}$	-	±20	mA
I <sub>CC</sub>	supply current		-	+50	mA
I <sub>GND</sub>	ground current		-50	-	mA
T <sub>stg</sub>	storage temperature		-65	+150	°C
P <sub>tot</sub>	total power dissipation	$T_{amb} = -40 \ ^{\circ}C$ to +125 $^{\circ}C$	[2] _	250	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

### 9. Recommended operating conditions

Table 6.	Recommended operating conditions							
Symbol	Parameter	Conditions	Min	Max	Unit			
V <sub>CC</sub>	supply voltage		0.8	3.6	V			
VI	input voltage		0	3.6	V			
Vo	output voltage	Active mode	0	$V_{CC}$	V			
		Power-down mode; $V_{CC} = 0 V$	0	3.6	V			
T <sub>amb</sub>	ambient temperature		-40	+125	°C			
$\Delta t / \Delta V$	input transition rise and fall rate	$V_{CC} = 0.8 V \text{ to } 3.6 V$	0	200	ns/V			

### Table 6. Recommended operating conditions



Low-power buffer

## **10. Static characteristics**

#### Table 7. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
T <sub>amb</sub> = 2	5 °C					
V <sub>IH</sub>	HIGH-level input voltage	$V_{CC} = 0.8 V$	$0.70 \times V_{CC}$	-	-	V
		$V_{CC} = 0.9 V$ to 1.95 V	$0.65 \times V_{CC}$	-	-	V
		$V_{CC}$ = 2.3 V to 2.7 V	1.6	-	-	V
		$V_{CC} = 3.0 V \text{ to } 3.6 V$	2.0	-	-	V
V <sub>IL</sub>	LOW-level input voltage	$V_{CC} = 0.8 V$	-	-	$0.30\times V_{CC}$	V
		$V_{CC} = 0.9 V$ to 1.95 V	-	-	$0.35 \times V_{CC}$	V
		$V_{CC}$ = 2.3 V to 2.7 V	-	-	0.7	V
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	-	-	0.9	V
√ <sub>ОН</sub>	HIGH-level output voltage	$V_I = V_{IH} \text{ or } V_{IL}$				
		$I_{O}$ = –20 $\mu A; V_{CC}$ = 0.8 V to 3.6 V	$V_{CC}-0.1$	-	-	V
		$I_{O} = -1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	$0.75 \times V_{CC}$	-	-	V
		$I_0 = -1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	1.11	-	-	V
		$I_{O}$ = -1.9 mA; $V_{CC}$ = 1.65 V	1.32	-	-	V
		$I_{O}$ = -2.3 mA; $V_{CC}$ = 2.3 V	2.05	-	-	V
		$I_{O} = -3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.9	-	-	V
		$I_{O} = -2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.72	-	-	V
		$I_{O} = -4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.6	-	-	V
V <sub>OL</sub>	LOW-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$				
		$I_{O}$ = 20 $\mu$ A; $V_{CC}$ = 0.8 V to 3.6 V	-	-	0.1	V
		I <sub>O</sub> = 1.1 mA; V <sub>CC</sub> = 1.1 V	-	-	$0.3 \times V_{CC}$	V
		I <sub>O</sub> = 1.7 mA; V <sub>CC</sub> = 1.4 V	-	-	0.31	V
		I <sub>O</sub> = 1.9 mA; V <sub>CC</sub> = 1.65 V	-	-	0.31	V
		$I_0 = 2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.31	V
		$I_0 = 3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.44	V
		$I_0 = 2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.31	V
		$I_0 = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.44	V
I	input leakage current	$V_I = GND$ to 3.6 V; $V_{CC} = 0$ V to 3.6 V	-	-	±0.1	μΑ
OFF	power-off leakage current	$V_1$ or $V_0 = 0$ V to 3.6 V; $V_{CC} = 0$ V	-	-	±0.2	μΑ
∆I <sub>OFF</sub>	additional power-off leakage current	$V_1 \text{ or } V_0 = 0 \text{ V to } 3.6 \text{ V};$ $V_{CC} = 0 \text{ V to } 0.2 \text{ V}$	-	-	±0.2	μA
СС	supply current	$V_{I} = GND \text{ or } V_{CC}; I_{O} = 0 \text{ A};$ $V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	-	-	0.5	μΑ
∆l <sub>CC</sub>	additional supply current		<u>[1]</u> -	-	40	μA
CI	input capacitance	$V_{CC}$ = 0 V to 3.6 V; $V_{I}$ = GND or $V_{CC}$	-	0.8	-	pF
Co	output capacitance	$V_0 = GND; V_{CC} = 0 V$	_	1.7	_	pF

 $T_{amb} = -40 \ ^{\circ}C \ to \ +85 \ ^{\circ}C$ 

74AUP1G34

Low-power buffer

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>IH</sub>	HIGH-level input voltage	$V_{CC} = 0.8 V$	$0.70 \times V_{CC}$	-	-	V
		$V_{CC} = 0.9 V$ to 1.95 V	$0.65 \times V_{CC}$	-	-	V
		$V_{CC}$ = 2.3 V to 2.7 V	1.6	-	-	V
		$V_{CC}$ = 3.0 V to 3.6 V	2.0	-	-	V
VIL	LOW-level input voltage	$V_{CC} = 0.8 V$	-	-	$0.30\times V_{CC}$	V
		$V_{CC} = 0.9 V$ to 1.95 V	-	-	$0.35 \times V_{CC}$	V
		$V_{CC}$ = 2.3 V to 2.7 V	-	-	0.7	V
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	-	-	0.9	V
√ <sub>ОН</sub>	HIGH-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$				
		$I_{O}$ = –20 $\mu\text{A};V_{CC}$ = 0.8 V to 3.6 V	$V_{CC}-0.1$	-	-	V
		$I_{O} = -1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	$0.7\times V_{CC}$	-	-	V
		$I_{O} = -1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	1.03	-	-	V
		$I_{O} = -1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	1.30	-	-	V
		$I_{O}$ = -2.3 mA; $V_{CC}$ = 2.3 V	1.97	-	-	V
		$I_{O} = -3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.85	-	-	V
		$I_{O} = -2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.67	-	-	V
		$I_{O} = -4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.55	-	-	V
/ <sub>OL</sub>	LOW-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$				
		$I_{O}$ = 20 $\mu$ A; $V_{CC}$ = 0.8 V to 3.6 V	-	-	0.1	V
		I <sub>O</sub> = 1.1 mA; V <sub>CC</sub> = 1.1 V	-	-	$0.3\times V_{CC}$	V
		$I_0 = 1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	-	-	0.37	V
		$I_0 = 1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	-	-	0.35	V
		$I_0 = 2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.33	V
		$I_0 = 3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.45	V
		$I_0 = 2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.33	V
		$I_0 = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.45	V
I	input leakage current	$V_{I}$ = GND to 3.6 V; $V_{CC}$ = 0 V to 3.6 V	-	-	±0.5	μΑ
OFF	power-off leakage current	$V_1$ or $V_0 = 0$ V to 3.6 V; $V_{CC} = 0$ V	-	-	±0.5	μΑ
\I <sub>OFF</sub>	additional power-off leakage current	$V_1$ or $V_0 = 0$ V to 3.6 V; $V_{CC} = 0$ V to 0.2 V	-	-	±0.6	μA
СС	supply current	$\label{eq:VI} \begin{array}{l} V_{I} = GND \text{ or } V_{CC}; \ I_{O} = 0 \ A; \\ V_{CC} = 0.8 \ V \text{ to } 3.6 \ V \end{array}$	-	-	0.9	μA
∕l <sup>CC</sup>	additional supply current	$V_{I} = V_{CC} - 0.6 \text{ V}; I_{O} = 0 \text{ A};$ $V_{CC} = 3.3 \text{ V}$	<u>[1]</u> -	-	50	μA

#### Table 7. Static characteristics ... continued

Low-power buffer

At recom	mended operating conditions	; voltages are referenced to GND (groun	d = 0 V).			
-	Parameter	Conditions	Min	Тур	Max	Unit
T <sub>amb</sub> = -	40 °C to +125 °C					
V <sub>IH</sub>	HIGH-level input voltage	$V_{CC} = 0.8 V$	$0.75\times V_{CC}$		-	V
		$V_{CC} = 0.9 V$ to 1.95 V	$0.70\times V_{CC}$	-	-	V
		$V_{CC}$ = 2.3 V to 2.7 V	1.6	-	-	V
		$V_{CC} = 3.0 V \text{ to } 3.6 V$	2.0	-	-	V
V <sub>IL</sub>	LOW-level input voltage	$V_{CC} = 0.8 V$	-	-	$0.25 \times V_{CC}$	V
		$V_{CC} = 0.9 V$ to 1.95 V	-	-	$0.30 \times V_{CC}$	V
		$V_{CC}$ = 2.3 V to 2.7 V	-	-	0.7	V
		$V_{CC} = 3.0 V \text{ to } 3.6 V$	-	-	0.9	V
V <sub>OH</sub>	HIGH-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$				
		$I_O$ = –20 $\mu\text{A};V_{CC}$ = 0.8 V to 3.6 V	$V_{CC}-0.11$	-	-	V
		$I_0 = -1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	$0.6\times V_{CC}$	-	-	V
		$I_0 = -1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	0.93	-	-	V
		$I_0 = -1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	1.17	-	-	V
		$I_{O}$ = -2.3 mA; $V_{CC}$ = 2.3 V	1.77	-	-	V
		$I_0 = -3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.67	-	-	V
		$I_0 = -2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.40	-	-	V
		$I_{O} = -4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.30	-	-	V
V <sub>OL</sub>	LOW-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$				
		$I_O$ = 20 $\mu A;V_{CC}$ = 0.8 V to 3.6 V	-	-	0.11	V
		$I_0 = 1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	-	-	$0.33 \times V_{CC}$	V
		$I_0 = 1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	-	-	0.41	V
		$I_0 = 1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	-	-	0.39	V
		$I_{O}$ = 2.3 mA; $V_{CC}$ = 2.3 V	-	-	0.36	V
		$I_0 = 3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.50	V
		$I_0 = 2.7$ mA; $V_{CC} = 3.0$ V	-	-	0.36	V
		$I_0 = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.50	V
I <sub>I</sub>	input leakage current	$V_{\rm I}$ = GND to 3.6 V; $V_{\rm CC}$ = 0 V to 3.6 V	-	-	±0.75	μΑ
I <sub>OFF</sub>	power-off leakage current	$V_{I}$ or $V_{O}$ = 0 V to 3.6 V; $V_{CC}$ = 0 V	-	-	±0.75	μΑ
$\Delta I_{OFF}$	additional power-off leakage current	$V_1 \text{ or } V_0 = 0 \text{ V to } 3.6 \text{ V};$ $V_{CC} = 0 \text{ V to } 0.2 \text{ V}$	-	-	±0.75	μA
I <sub>CC</sub>	supply current	$\label{eq:VI} \begin{array}{l} V_{I} = GND \text{ or } V_{CC};  I_{O} = 0 \; A; \\ V_{CC} = 0.8 \; V \; \text{to} \; 3.6 \; V \end{array}$	-	-	1.4	μΑ
$\Delta I_{CC}$	additional supply current	$V_{I} = V_{CC} - 0.6 \text{ V}; I_{O} = 0 \text{ A};$ $V_{CC} = 3.3 \text{ V}$	<u>[1]</u> -	-	75	μA

#### Table 7. Static characteristics ... continued

[1] One input at  $V_{CC}$  – 0.6 V, other input at  $V_{CC}$  or GND.

## **11. Dynamic characteristics**

#### Table 8. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 8.

Symbol	Parameter	Conditions	-	Г <sub>ать</sub> = 25	°C	Ta	<sub>mb</sub> = -40 '	°C to +	125 °C	Unit
				ו Typ <mark>[1]</mark>	Max	Min	Max (85 °C)	Min	Max (125 °C)	
C <sub>L</sub> = 5 p	F									
t <sub>pd</sub>	propagation	A to Y; see Figure 7	[2]							
	delay	$V_{CC} = 0.8 V$	-	15.0	-	-	-	-	-	ns
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$	2.0	6 4.7	9.2	2.0	10.0	2.0	11.0	ns
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$	2.1	3.4	5.7	1.6	6.5	1.6	7.2	ns
		$V_{CC}$ = 1.65 V to 1.95 V	1.8	3 2.9	4.5	1.4	5.2	1.4	5.8	ns
		$V_{CC}$ = 2.3 V to 2.7 V	1.	5 2.3	3.5	1.2	4.2	1.2	4.6	ns
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	1.4	2.1	3.2	1.0	3.8	1.0	4.2	ns
C <sub>L</sub> = 10	pF									
t <sub>pd</sub>	propagation	A to Y; see Figure 7	[2]							
	delay	$V_{CC} = 0.8 V$	-	18.4	-	-	-	-	-	ns
		$V_{CC}$ = 1.1 V to 1.3 V	3.2	2 5.6	10.9	2.3	11.8	2.3	13.1	ns
		$V_{CC} = 1.4 \text{ V}$ to 1.6 V	2.0	6 4.1	6.7	1.9	7.7	1.9	8.5	ns
		$V_{CC}$ = 1.65 V to 1.95 V	2.3	3 3.4	5.3	1.7	6.2	1.7	6.9	ns
		$V_{CC}$ = 2.3 V to 2.7 V	2.0	) 2.9	4.2	1.5	5.0	1.5	5.5	ns
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	1.	2.6	3.8	1.4	4.6	1.4	5.1	ns
C <sub>L</sub> = 15	pF									
t <sub>pd</sub>	propagation	A to Y; see Figure 7	[2]							
	delay	$V_{CC} = 0.8 V$	-	21.9	-	-	-	-	-	ns
		$V_{CC}$ = 1.1 V to 1.3 V	3.0	6.4	12.6	2.6	13.8	2.6	15.2	ns
		$V_{CC}$ = 1.4 V to 1.6 V	3.0	) 4.6	7.6	2.2	8.9	2.2	9.8	ns
		$V_{CC}$ = 1.65 V to 1.95 V	2.0	3.9	6.0	2.0	7.2	2.0	7.9	ns
		$V_{CC}$ = 2.3 V to 2.7 V	2.3	3 3.3	4.8	1.8	5.7	1.8	6.3	ns
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	2.	3.1	4.2	1.6	5.0	1.6	5.5	ns
C <sub>L</sub> = 30	pF									
t <sub>pd</sub>	propagation	A to Y; see Figure 7	[2]							
	delay	$V_{CC} = 0.8 V$	-	32.1	-	-	-	-	-	ns
		$V_{CC}$ = 1.1 V to 1.3 V	4.8	8 8.7	16.3	3.6	18.9	3.6	20.8	ns
		$V_{CC}$ = 1.4 V to 1.6 V	4.0	6.2	10.3	3.4	12.2	3.4	13.4	ns
		V <sub>CC</sub> = 1.65 V to 1.95 V	3.0	5.2	8.1	3.2	9.8	3.2	10.8	ns
		$V_{CC}$ = 2.3 V to 2.7 V	3.0	) 4.4	6.4	2.7	7.7	2.7	8.5	ns

Low-power buffer

Symbol	Parameter	Conditions	Conditions		T <sub>amb</sub> = 25 °C		Tai	mb = -40 °	°C to +	125 °C	Unit
			Min	Typ <mark>[1]</mark>	Max	Min	Max (85 °C)	Min	Max (125 °C)		
10	power dissipation capacitance	$f_i = 1 \text{ MHz};$ V <sub>1</sub> = GND to V <sub>CC</sub>	<u>[3]</u>								
		$V_{CC} = 0.8 V$		-	2.5	-	-	-	-	-	pF
		$V_{CC}$ = 1.1 V to 1.3 V		-	2.6	-	-	-	-	-	pF
		$V_{CC} = 1.4 \text{ V}$ to 1.6 V		-	2.7	-	-	-	-	-	pF
		$V_{CC}$ = 1.65 V to 1.95 V		-	2.9	-	-	-	-	-	pF
		$V_{CC}$ = 2.3 V to 2.7 V		-	3.4	-	-	-	-	-	pF
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$		-	4.0	-	-	-	-	-	pF

#### Table 8. Dynamic characteristics ...continued

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 8.

[1] All typical values are measured at nominal  $V_{\mbox{CC}}.$ 

[2]  $t_{pd}$  is the same as  $t_{PLH}$  and  $t_{PHL}$ .

[3]  $C_{PD}$  is used to determine the dynamic power dissipation ( $P_D$  in  $\mu W$ ).

 $P_{D} = C_{PD} \times V_{CC}^{2} \times f_{i} \times N + \Sigma (C_{L} \times V_{CC}^{2} \times f_{o}) \text{ where:}$ 

 $f_i$  = input frequency in MHz;

 $f_o = output frequency in MHz;$ 

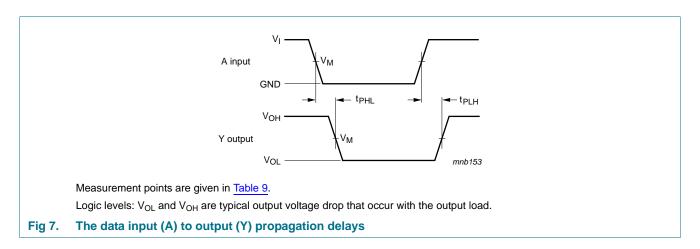
 $C_L$  = output load capacitance in pF;

V<sub>CC</sub> = supply voltage in V;

N = number of inputs switching;

 $\Sigma(C_L \times V_{CC}^2 \times f_o)$  = sum of outputs.

### 12. Waveforms

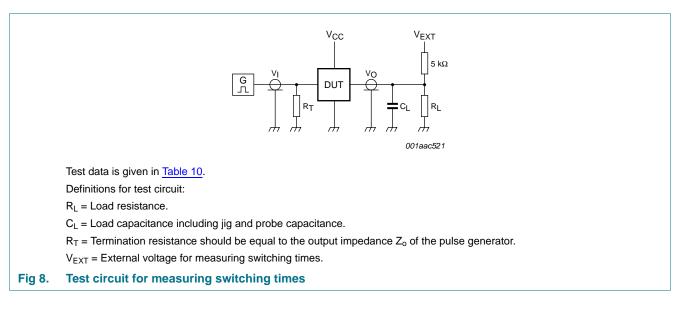


#### Table 9. Measurement points

Supply voltage	Output	Input					
V <sub>CC</sub>	V <sub>M</sub>	V <sub>M</sub>	VI	$t_r = t_f$			
0.8 V to 3.6 V	$0.5\times V_{CC}$	$0.5\times V_{CC}$	V <sub>CC</sub>	$\leq$ 3.0 ns			



#### Low-power buffer



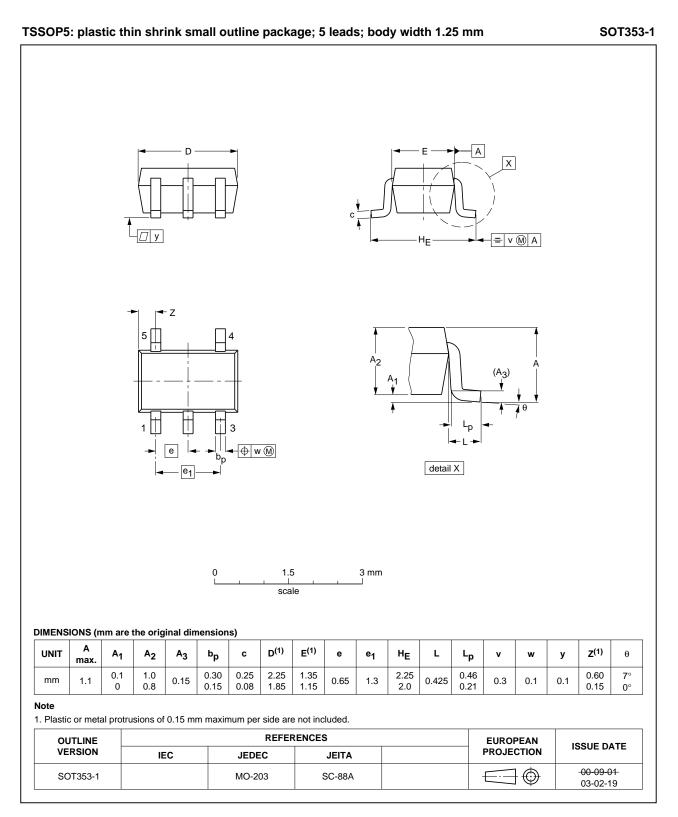
#### Table 10.Test data

Supply voltage	Load		V <sub>EXT</sub>		
V <sub>cc</sub>	CL	R <sub>L</sub> [1]	t <sub>PLH</sub> , t <sub>PHL</sub>	t <sub>PZH</sub> , t <sub>PHZ</sub>	t <sub>PZL</sub> , t <sub>PLZ</sub>
0.8 V to 3.6 V	5 pF, 10 pF, 15 pF and 30 pF	5 k $\Omega$ or 1 M $\Omega$	open	GND	$2 \times V_{CC}$

[1] For measuring enable and disable times  $R_L = 5 k\Omega$ , for measuring propagation delays, setup and hold times and pulse width  $R_L = 1 M\Omega$ .

Low-power buffer

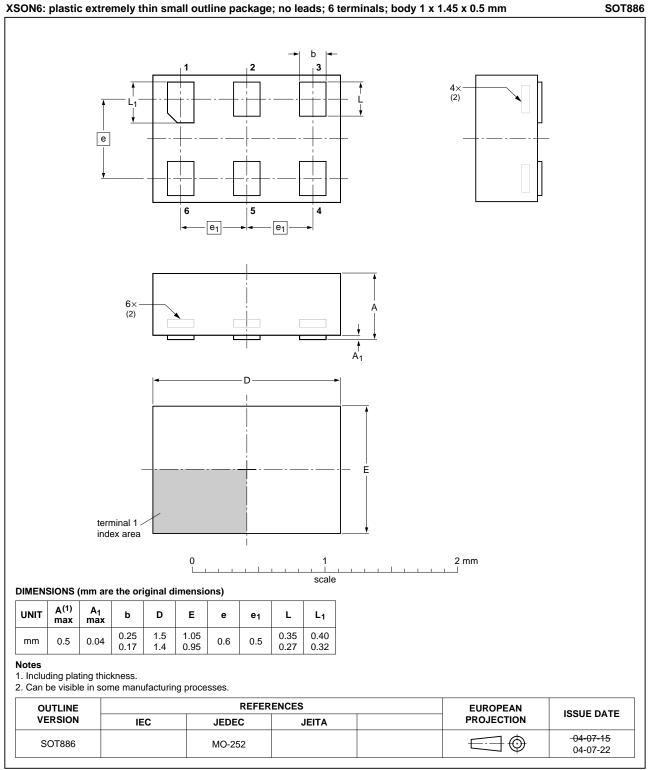
### 13. Package outline



#### Fig 9. Package outline SOT353-1 (TSSOP5)

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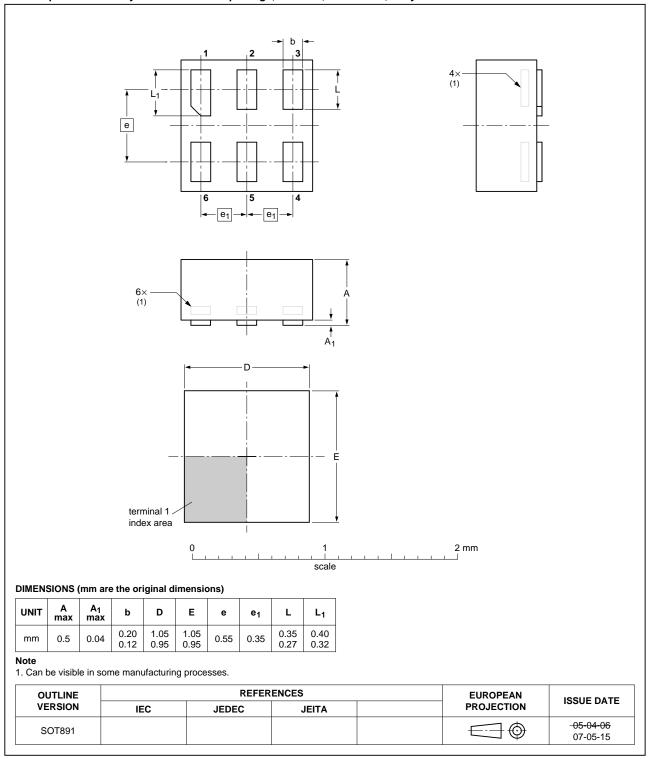
74AUP1G34



XSON6: plastic extremely thin small outline package; no leads; 6 terminals; body 1 x 1.45 x 0.5 mm

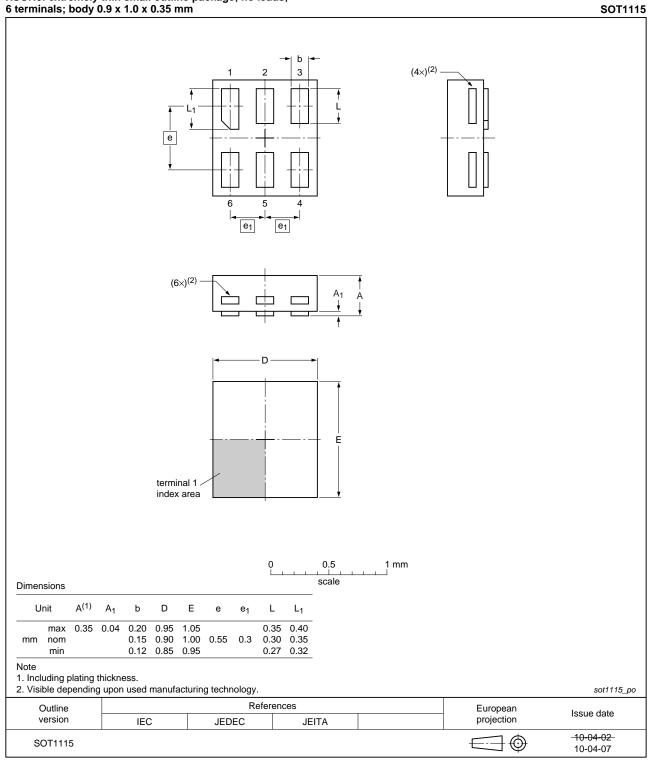
#### Fig 10. Package outline SOT886 (XSON6)

SOT891



## XSON6: plastic extremely thin small outline package; no leads; 6 terminals; body 1 x 1 x 0.5 mm

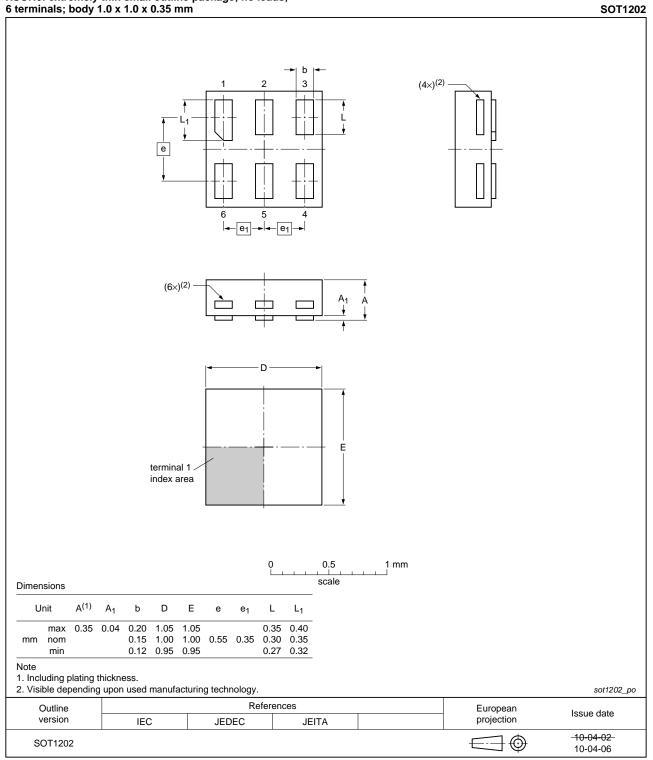
#### Fig 11. Package outline SOT891 (XSON6)



# XSON6: extremely thin small outline package; no leads; 6 terminals; body 0.9 x 1.0 x 0.35 mm

Fig 12. Package outline SOT1115 (XSON6)





XSON6: extremely thin small outline package; no leads; 6 terminals; body 1.0 x 1.0 x 0.35 mm

Fig 13. Package outline SOT1202 (XSON6)



### 14. Abbreviations

Table 11. Abbreviations		
Acronym	Description	
CDM	Charged Device Model	
DUT	Device Under Test	
ESD	ElectroStatic Discharge	
HBM	Human Body Model	
MM	Machine Model	

# **15. Revision history**

Table 12. Revisio	n history			
Document ID	Release date	Data sheet status	Change notice	Supersedes
74AUP1G34 v.4	20100714	Product data sheet	-	74AUP1G34 v.3
Modifications:	••	number 74AUP1G34GN (SOT number 74AUP1G34GS (SOT		
74AUP1G34 v.3	20080814	Product data sheet	-	74AUP1G34 v.2
74AUP1G34 v.2	20060704	Product data sheet	-	74AUP1G34 v.1
74AUP1G34 v.1	20050804	Product data sheet	-	-

### 16. Legal information

### 16.1 Data sheet status

Document status[1][2]	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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[2] The term 'short data sheet' is explained in section "Definitions".

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### **18. Contents**

1	General description 1
2	Features and benefits 1
3	Ordering information 2
4	Marking 2
5	Functional diagram 2
6	Pinning information 3
6.1	Pinning 3
6.2	Pin description 3
7	Functional description 3
8	Limiting values 4
9	Recommended operating conditions 4
10	Static characteristics 5
11	Dynamic characteristics 8
12	Waveforms
13	Package outline 11
14	Abbreviations
15	Revision history 16
16	Legal information
16.1	Data sheet status 17
16.2	Definitions
16.3	Disclaimers
16.4	Trademarks 18
17	Contact information 18
18	Contents 19

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